



Form PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)	Docket Number 416272004201	Application Number 10/729,726
	Applicant Sung-Mo KANG and Seung-Moon YOO	
	Filing Date December 5, 2003	Group Art Unit 2838 2816
	Mailing Date April 5, 2004	

U.S. PATENT DOCUMENTS

Examiner Initials	Ref. No.	Date	Document No.	Name	Class	Subclass	Filing Date If Appropriate
JZ	1.	5/19/1992	5,115,150	Ludwig, Mark A.	—	—	
see PTO-892	2.	9/29/1992	5,151,620	Lin, Ming-Zen	—	—	
JZ	3.	12/29/1992	5,175,448	Fujii	—	—	
JZ	4.	8/26/1997	5,661,419	Bhagwan	—	—	
892	5.	3/9/1999	5,880,604	Kawahara et al.	—	—	
see PTO-892	6.	4/11/2000	6,049,245	Son et al.	—	—	
892	7.	8/22/2000	6,107,869	Horiguchi et al.	—	—	
892	8.	2/20/2001	6,191,615	Koga, Hiroshi	—	—	
JZ	9.	3/20/2001	6,204,696	Krishnamurthy et al.	—	—	
JZ	10.	4/9/2002	6,370,052 B1	Hsu et al.	—	—	
892	11.	6/11/2002	6,404,269	Voldman	—	—	
892	12.	6/25/2002	6,411,157	Hsu et al.	—	—	
JZ	13.	8/27/2002	6,442,086 B1	Dean	—	—	
JZ	14.	12/2002	6,492,837 B1	Narendra et al.	—	—	
JZ	15.	5/21/2002	10/153,158	Yoo et al.	—	—	

FOREIGN PATENT DOCUMENTS

Examiner Initials	Ref. No.	Date	Document No.	Country	Class	Subclass	Translation YES NO

OTHER DOCUMENTS

(including author, title, Date, Pertinent Pages, Etc.)

Examiner Initials	Ref. No.	Title
JZ	16.	M. Anis et al., "Dynamic and Leakage Power Reduction in MTCMOS Circuits Using an Automated Efficient Gate Clustering Technique", IEEE, June 10-14, 2002, New Orleans, Louisiana, pp. 480-485.
JZ	17.	Assaderaghi et al., "A Dynamic Threshold Voltage MOSFET (DTMOS) for Ultra-Low

EXAMINER: Jeffrey Zweizig

DATE CONSIDERED: 11/22/04

EXAMINER: Initial if citation considered, whether or not the citation conforms with MPEP 609. Draw a line through the citation if not in conformance and not considered. Include a copy of this form with next communication to applicant.

x- ~~Did not receive~~

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cont		Voltage Operation", <i>International Electron Devices Meeting, Digest of Technical Papers</i> , pages 809-812, June 1994.
JZ	18.	J. Burr and J. Scott, "A 200mV Self-Testing Encoder/Decoder using Stanford Ultra-Low-Power CMOS", <i>ISSCC Digest of Technical Papers</i> , pages 84-85, February 1994.
JZ	19.	Mark N. Horenstein, <i>Microelectronic Circuits & Devices</i> , 1996, pgs. 240-250.
JZ	20.	M. Horiguchi et al., "Switched-Source-Impedance CMOS Circuit for Low Standby Subthreshold Current Giga-Scale LSI's", <i>IEEE Journal of Solid State Circuits</i> , 28(11):1131-1135, November 1993.
JZ	21.	T. Iwata et al., "Gate-Over-Driving CMOS Architecture for 0.5V Single-Power-Supply-Operated Devices", <i>ISSCC Digest of Technical Papers</i> , pages 290-291, February 1997.
JZ	22.	Kawaguchi et al., "A CMOS Scheme for 0.5V Supply Voltage with Pico-Ampere Standby Current", <i>ISSCC Digest of Technical Papers</i> , pages 192-193, February 1998.
JZ	23.	T. Kuroda et al., "A 0.9V 150MHz 10mW 4mm ² 2D Discrete Cosine Transform Core Processor with Variable-Threshold-Voltage Scheme", <i>ISSCC Digest of Technical Papers</i> , pages 166-167, February 1996.
JZ	24.	Mutoh et al., "1-V Power Supply High-Speed Digital Circuit Technology with Multithreshold-Voltage CMOS", <i>IEEE Journal of Solid State Circuits</i> , 30(8): 845-854, August 1995.
JZ	25.	K. Seta et al., "50% Active-Power Saving without Speed Degradation Using Standby Power Reduction (SPR) Circuit", in <i>ISSCC Digest of Technical Papers</i> , pages 318-319, February 1995.
JZ	26.	S. Shigematsu et al., "A 1-V High-Speed MTCMOS Circuit Scheme for Power-Down Application Circuits", <i>IEEE Journal of Solid State Circuits</i> , 32(6):861-869, June 1997.
JZ	27.	Seung-Moon Yoo et al., "New High Performance Sub-1V Circuit Technique with Reduced Standby Current and Robust Data Holding", <i>IEEE International Symposium on Circuits and Systems</i> , May 28-31, 2000, Geneva, Switzerland (Pages 1-4)
considered but	28.	Notice of Allowance and Fee due, Notice of Allowability and Examiner's Amendment for Application Ser. no. 10/153,158, 6 pgs.
not printed	29.	Amendment A for the U. S. patent application 10/153,158, Yoo et al., filed 5/21/2002, 13 pgs. 4/9/2003.
JZ	30.	International Search Report mailed on February 25, 2004, for PCT/US03/24976 filed on August 8, 2003, 7 pgs.

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ALTERNATIVE TO PTO/SB/06a/b (08-03)

Substitute for form 1449/PTD				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Application Number	10/729,726
				Filing Date	December 5, 2003
				First Named Inventor	Sung-Mo KANG
				Art Unit	2816
				Examiner Name	J. S. Zweizig
Sheet	1	of	1	Attorney Docket Number	416272004201

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.*	Document Number Number-Kind Code* (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
JZ	1.	6,759,873	7/6/2004	Kang et al.	

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No.*	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T*
		Country Code*	Number*-Kind Code* (if known)				

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.*	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T*

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* Applicant's unique citation designation number (optional). * Applicant is to place a check mark here if English language Translation is attached.

Examiner Signature	Jeffrey Zweizig	Date Considered	11/22/04
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6f-1819144